



12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN#20260617001.2
Qualification of RFAB as an additional Fab site,
Die Revision and CDAT as additional
Assembly/Test site option for select devices
Change Notification / Sample Request

Date: June 18, 2026

To: MOUSER PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

Texas Instruments requires acknowledgement of receipt of this notification within 60 days of the date of this notice. Lack of acknowledgement of this notice within 60 days constitutes acceptance and approval of this change. If samples or additional data are required, requests must be received within 60 days of this notification.

The changes discussed within this PCN will not take effect any earlier than the proposed first ship date on Page 3 of this notification, unless customer agreement has been reached on an earlier implementation of the change.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the change management team.

For sample requests or sample related questions, contact your local Field Sales Representative.

TI values customer engagement and feedback related to TI changes. Customers should contact TI if there are questions or concerns regarding a change notification.

Sincerely,

Change Management Team
SC Business Services

20260617001.2
Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, you have recently purchased these devices. The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
INA199C2QDCKRQ1	INA199C2QDCKRQ1
INA199B2QDCKRQ1	INA199B2QDCKRQ1
INA199B1QDCKRQ1	INA199B1QDCKRQ1
INA199C3QDCKRQ1	INA199C3QDCKRQ1
INA199C1QDCKRQ1	INA199C1QDCKRQ1

Technical details of this Product Change follow on the next page(s).

PCN Number:	20260617001.2	PCN Date:	June 18, 2026																										
Title:	Qualification of RFAB as an additional Fab site, Die Revision and CDAT as additional Assembly/Test site option for select devices																												
Customer Contact:	Change Management Team	Dept:	Quality Services																										
Proposed 1st Ship Date:	December 15, 2026	Sample requests accepted until:	August 17, 2026*																										
*Sample requests received after August 17, 2026 will not be supported.																													
Change Type:																													
<input checked="" type="checkbox"/>	Assembly Site	<input checked="" type="checkbox"/>	Design																										
<input checked="" type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Data Sheet																										
<input checked="" type="checkbox"/>	Assembly Materials	<input type="checkbox"/>	Part number change																										
<input type="checkbox"/>	Mechanical Specification	<input checked="" type="checkbox"/>	Test Site																										
<input checked="" type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process																										
<input type="checkbox"/>		<input type="checkbox"/>	Wafer Bump Material																										
<input type="checkbox"/>		<input type="checkbox"/>	Wafer Bump Process																										
<input checked="" type="checkbox"/>		<input checked="" type="checkbox"/>	Wafer Fab Site																										
<input checked="" type="checkbox"/>		<input checked="" type="checkbox"/>	Wafer Fab Material																										
<input checked="" type="checkbox"/>		<input checked="" type="checkbox"/>	Wafer Fab Process																										
PCN Details																													
Description of Change:																													
Texas Instruments is pleased to announce the qualification of RFAB as an additional Fab site and CDAT as additional Assembly/Test site option for the devices listed below.																													
<table border="1" style="width: 100%; border-collapse: collapse;"> <thead> <tr> <th colspan="3">Current Fab Site</th> <th colspan="3">Additional Fab site</th> </tr> <tr> <th>Current Fab Site</th> <th>Process</th> <th>Wafer Diameter</th> <th>Additional Fab site</th> <th>Process</th> <th>Wafer Diameter</th> </tr> </thead> <tbody> <tr> <td style="text-align: center;">AIZU</td> <td style="text-align: center;">50HPA07</td> <td style="text-align: center;">200mm</td> <td style="text-align: center;">RFAB</td> <td style="text-align: center;">LBC9</td> <td style="text-align: center;">300mm</td> </tr> </tbody> </table>						Current Fab Site			Additional Fab site			Current Fab Site	Process	Wafer Diameter	Additional Fab site	Process	Wafer Diameter	AIZU	50HPA07	200mm	RFAB	LBC9	300mm						
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Construction differences as follows:																													
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Qual details are provided in the Qual Data Section.																													
Reason for Change:																													
Supply Continuity																													
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):																													
Review the SDP for full evaluation of the change based on the customer use case.																													
Impact on Environmental Ratings																													
Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.																													
RoHS		REACH		Green Status																									
<input checked="" type="checkbox"/> No Change		<input checked="" type="checkbox"/> No Change		<input checked="" type="checkbox"/> No Change																									
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Changes to product identification resulting from this PCN:																													
Fab Site																													

Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
AIZU	CU2	JPN	Aizuwakamatsu-shi
RFAB	RFB	USA	Richardson

Die Rev:**Current****New**

Die Rev [2P]	Die Rev [2P]
A	A

Assembly Site Information:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
TFME	NFM	CHN	Chongchuan
TI Chengdu	CDA	CHN	Chengdu

Sample product shipping label (not actual product label):

(1P) SN74LS07NSR
 (Q) 2000 (D) 0336
 (31T) LOT: 3959047MLA
 (4W) TKY (1T) 7523483SI2
 (P)
 (2P) REV: (V) 8899317
 (20L) CSO: SHE (21L) CCO: USA
 (22L) ASO: MLA (23L) ACO: MYS

Product Affected:

INA199A1QDCKRQ1	INA199B1QDCKRQ1	INA199C1QDCKRQ1
INA199A2QDCKRQ1	INA199B2QDCKRQ1	INA199C2QDCKRQ1
INA199A3QDCKRQ1	INA199B3QDCKRQ1	INA199C3QDCKRQ1

Qualification Report

Automotive Qualification Summary

(As per AEC-Q100 Rev. J and JEDEC Guidelines)

Approve Date 25-March-2026

Product Attributes

Attributes	Qual Device: INA199A1QDCKRQ1	Qual Device: INA199A2QDCKRQ1	Qual Device: INA199A3QDCKRQ1	QBS Process Reference: OPA2991QDCKRQ1	QBS Package Reference: DRV5013ADEDBZRQ1	QBS Package Reference: TPS388REG01DBVRQ1	QBS Package Reference: TPS388PH300BVRQ1	QBS Product Reference: OPA992QDCKRQ1	QBS Package Reference: TX5011QDCKRQ1	QBS Package Reference: OPA992QDCKRQ1	QBS Package Reference: TLV911QDCKRQ1	QBS Package Reference: SN74LVC1G16DCKRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 0	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Signal Chain	Signal Chain	Signal Chain	Signal Chain	Signal Chain	Power Management	Power Management	Signal Chain	Signal Chain	Signal Chain	Signal Chain	Logic
Wafer Fab Supplier	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB
Assembly Site	CDAT	CDAT	CDAT	HPTFAT	CDAT	CDAT	CDAT	CDAT	CDAT	CDAT	CDAT	CDAT
Package Group	SOT	SOT	SOT	VSSOP	SOT	SOT	SOT	SOT	SOT	SOT	SOT	SOT
Package Designator	DCK	DCK	DCK	DKK	DBZ	DBV	DBV	DBV	DCK	DCK	DCK	DCK
Pin Count	6	6	6	8	3	6	5	5	6	5	5	5

QBS: Qual By Similarity, also known as Generic Data
 Qual Device INA199A1QDCKRQ1 is qualified at MSL1 260C
 Qual Device INA199A2QDCKRQ1 is qualified at MSL1 260C
 Qual Device INA199A3QDCKRQ1 is qualified at MSL1 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	ES Lot	Test Name	Condition	Duration	Qual Device: INA199A1QDCKRQ1	Qual Device: INA199A2QDCKRQ1	Qual Device: INA199A3QDCKRQ1	QBS Process Reference: OPA2991QDCKRQ1	QBS Package Reference: DRV5013ADEDBZRQ1	QBS Package Reference: TPS388REG01DBVRQ1	QBS Package Reference: TPS388PH300BVRQ1	QBS Product Reference: OPA992QDCKRQ1	QBS Package Reference: TX5011QDCKRQ1	QBS Package Reference: OPA992QDCKRQ1	QBS Package Reference: TLV911QDCKRQ1	QBS Package Reference: SN74LVC1G16DCKRQ1	
Test Group A - Accelerated Environment Stress Tests																				
PC	A1	JEDEC J-STD-022-A113	3	77	Preconditioning	MSL1 260C	-	32310	-	-	-	32310	32310	1770	32310	1770	32310	32310	15080	106
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	110C/85%RH	264 Hours	-	-	-	-	-	-	-	1770	-	-	-	-	-
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	1770	-	-	-	32310	32310	1770	32310	1770 ¹	32310	-	1770	1770
ACM/HAST	A3	JEDEC JESD22-A110/JEDEC JESD22-A113	3	77	Unbiased HAST	110C/85%RH	264 Hours	-	-	-	-	-	-	-	1770	-	-	-	-	-
ACM/HAST	A3	JEDEC JESD22-A110/JEDEC JESD22-A113	3	77	Unbiased HAST	130C/85%RH	96 Hours	1770	-	-	-	32310	32310	1770	32310	-	32310	32310	1770	1770
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	55C/150C	1500 Cycles	-	-	-	-	-	32310	-	-	-	-	-	-	-
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	65C/150C	500 Cycles	-	-	-	-	32310	-	1770	32310	1770 ²	32310	32310	1770	1770
TC-BP	A4	ML-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	150	-	-	-	150	150	150	150	150	-	150	150	
TC-SAM	A4	-	3	3	Post TC SAM	<50% delamination	-	-	-	-	-	-	-	-	-	-	-	-	-	1/120
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	1450	-	-	-	-	1450	-	-	31350	1450	31350	-	1450
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	2000 Hours	-	-	-	-	31350	-	-	-	-	-	-	-	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	630 Hours	-	-	-	-	31350	-	-	-	-	-	-	-	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	176C	500 Hours	-	-	-	-	-	-	-	-	-	-	-	1770	-
Test Group B - Accelerated Lifetime Simulation Tests																				
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	1770	-	-	-	-	-	-	32310	-	32310	-	-	-
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	150C	1000 Hours	-	-	-	-	-	1770	-	-	-	-	-	-	-
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	150C	300 Hours	-	-	-	-	-	-	-	1770	-	-	-	1770	1770
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	150C	408 Hours	-	-	-	-	32310	-	-	-	-	-	-	-	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	-	-	-	-	324000	-	-	-	-	-	-	-	-
Test Group C - Package Assembly Integrity Tests																				
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	1000	-	-	-	3900	3900	1000	3900	1000	3900	3900	-	1000	1000
WBP	C2	ML-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	1000	-	-	-	3900	3900	1000	3900	1000	3900	3900	-	1000	1000
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	-	1150	1150	-	-	1150	-	-	-	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	-	1150	1150	-	-	1150	-	-	-	1150	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	1/100	-	-	3300	3300	1/100	3300	1/100	3300	-	1/100	1/100	
Test Group D - Die Fabrication Reliability Tests																				
EM	D1	JESD64	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
TDOB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
Test Group E - Electrical Verification Tests																				
ESD	E2	AEC Q100-002	1	3	ESD HBM	2000 Volts	-	-	-	-	1/30	1/30	1/30	-	1/30	1/30	-	1/30	1/30	
ESD	E2	AEC Q100-002	1	3	ESD HBM	3500 Volts	1/30	-	-	-	-	-	-	-	-	-	-	-	-	
ESD	E3	AEC Q100-011	1	3	ESD CDM	100 Volts	1/30	-	-	-	1/30	1/30	1/30	-	1/30	1/30	-	1/30	1/30	

Type	#	Test Spec	Min Lot Qty	SS Lot	Test Name	Condition	Duration	Qual Device: INA199A1Q00CKRQ1	Qual Device: INA199A2Q00CKRQ1	Qual Device: INA199A3Q00CKRQ1	QDS Process Reference: QPS2991Q00CKRQ1	QBS Package Reference: DRV9013ADEDB2RQ1	QBS Package Reference: TPS3808EG01DBVRQ1	QBS Package Reference: TPS3846PH300BVRQ1	QDS Product Reference: QPS992Q00BVRQ1	QBS Package Reference: TXS0101Q00CKRQ1	QBS Package Reference: QPS992Q00BVRQ1	QBS Package Reference: TLV3511Q00CKRQ1	QBS Package Reference: SN74VLC1G1600CKRQ1	
ESD	E3	AEC-Q100-011	1	3	ESD CDM	Corner pins	750 Volts	1000	-	-	-	-	-	-	-	-	-	-	-	-
LU	E4	AEC-Q100-004	1	3	Latch-Up	Per AEC-Q100-004	-	1000	-	-	100	100	100	-	100	100	-	100	100	100
ED	E5	AEC-Q100-009	3	30	Electrical Distributions	Cpk=1.67 Room, hot, and cold	-	1000	1000	1000	3000	2000	1000	3000	1000	3000	-	3000	1000	

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C

Grade 1 (or Q): -40C to +125C

Grade 2 (or T): -40C to +105C

Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2411-032

[1]-EIPD induced during handling. See 8D Report.

[2]-EIPD induced during handling. See 8D Report.

Qualification Report Automotive Qualification Summary (As per AEC and JEDEC Guidelines)

Q006 SOT at CDAT

Approve Date 25-March-2026

Product Attributes

Attributes	Qual Device: INA199A1Q00CKRQ1	Qual Device: INA199A2Q00CKRQ1	Qual Device: INA199A3Q00CKRQ1	QBS Package Reference: DRV9013ADEDB2RQ1	QBS Package Reference: TPS3808EG01DBVRQ1	QBS Package Reference: TPS3846PH300BVRQ1	QBS Package Reference: TXS0101Q00CKRQ1	QBS Package Reference: QPS992Q00BVRQ1	QBS Package Reference: TLV3511Q00CKRQ1	QBS Package Reference: SN74VLC1G1600CKRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 150	-40 to 125	-40 to 125	-40 to 125	-40 to 150	-40 to 125	-40 to 125
Product Function	Signal Chain	Signal Chain	Signal Chain	Signal Chain	Power Management	Power Management	Logic	Signal Chain	Signal Chain	Logic
Wafer Fab Supplier	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB
Assembly Site	CDAT	CDAT	CDAT	CDAT	CDAT	CDAT	CDAT	CDAT	CDAT	CDAT
Package Group	SOT	SOT	SOT	SOT	SOT	SOT	SOT	SOT	SOT	SOT
Package Designator	DCK	DCK	DCK	DBZ	DBV	DBV	DCK	DCK	DCK	DCK
Pin Count	6	6	6	3	6	5	6	5	5	5

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS Lot	Test Name	Condition	Duration	Qual Device: INA199A1Q00CKRQ1	Qual Device: INA199A2Q00CKRQ1	Qual Device: INA199A3Q00CKRQ1	QBS Reference: DRV9013ADEDB2RQ1	QBS Reference: TPS3808EG01DBVRQ1	QBS Reference: TPS3846PH300BVRQ1	QBS Reference: TXS0101Q00CKRQ1	QBS Reference: QPS992Q00BVRQ1	QBS Reference: TLV3511Q00CKRQ1	QBS Reference: SN74VLC1G1600CKRQ1
Test Group A - Accelerated Environment Stress Tests																	
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 250C	-	3/2310	-	-	3/2310	1/770	3/2310	3/2310	3/2310	-	-
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/660	-	-	3/660	1/220	3/660	3/660	3/660	-	-
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/660	-	-	3/660	1/220	3/660	3/660	3/660	-	-
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-	-	3/2310	1/770	3/2310	3/2310	-	-	-
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-	-	-	3/30	1/10	3/30	3/30	-	-	-
HAST	A2.1.3	-	3	3	Wire Bond Shear, post bHAST, 1X	Post stress	-	-	-	-	3/90	1/30	3/90	3/90	-	-	-
HAST	A2.1.4	-	3	3	Bond Pull over 50th, post bHAST, 1X	Post stress	-	-	-	-	3/90	1/30	3/90	3/90	-	-	-
HAST	A2.1.5	-	3	3	Bond Pull over Ball, post bHAST, 1X	Post stress	-	-	-	-	3/90	1/30	3/90	3/90	-	-	-
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	-	-	-	3/2310	1/770	3/2310	3/2310	-	-	-
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST, 2X	Review for delamination	Completed	-	-	-	3/660	1/220	3/660	3/660	-	-	-
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	-	-	-	3/30	1/10	3/30	3/30	-	-	-
HAST	A2.2.3	-	3	3	Wire Bond Shear, post bHAST, 2X	Post stress	-	-	-	-	3/90	1/30	3/90	3/90	-	-	-
HAST	A2.2.4	-	3	3	Bond Pull over 50th, post bHAST, 2X	Post stress	-	-	-	-	3/90	1/30	3/90	3/90	-	-	-
HAST	A2.2.5	-	3	3	Bond Pull over Ball, post bHAST, 2X	Post stress	-	-	-	-	3/90	1/30	3/90	3/90	-	-	-
TC	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-55C/150C	1500 Cycles	-	-	-	3/2310	-	-	-	-	-	-
TC	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	-	-	1/770	3/2310	3/2310	3/2310	3/2310	-	-
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	3/660	-	-	-	1/220	3/660	3/660	3/660	-	-

TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	3300	-	-	-	1/10	3300	3300	-	-	-	
TC	A4.1.3	-	3	3	Wire Bond Shear, post TC, 1X	Post stress	-	3900	-	-	-	1/30	3900	3900	-	-	-	
TC	A4.1.4	-	3	3	Bond Pull over 58kth, post TC, 1X	Post stress	-	3900	-	-	-	1/30	3900	3900	3900	-	-	
TC	A4.1.5	-	3	3	Bond Pull over Ball, post TC, 1X	Post stress	-	3900	-	-	-	1/30	3900	3900	-	-	-	
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-55C/150C	1000 Cycles	-	-	-	302310	-	-	-	-	-	-	
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	-	-	-	-	1/770	302310	302310	302310	-	-	
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	500 Cycles	302310	-	-	-	-	-	-	-	-	-	
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	-	-	-	3660	1220	3660	3660	3660	-	-	
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	-	-	-	330	1/10	330	330	-	-	-	
TC	A4.2.3	-	3	3	Wire Bond Shear, post TC, 2X	Post stress	-	-	-	-	390	1/30	390	390	-	-	-	
TC	A4.2.4	-	3	3	Bond Pull over 58kth, post TC, 2X	Post stress	-	-	-	-	390	1/30	390	390	390	-	-	
TC	A4.2.5	-	3	3	Bond Pull over Ball, post TC, 2X	Post stress	-	-	-	-	390	1/30	390	390	-	-	-	
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	-	-	-	-	1450	31350	31350	-	-	-	
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	2000 Hours	-	-	-	31350	-	-	-	-	-	-	
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	630 Hours	-	-	-	-	-	-	-	-	-	-	
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	-	-	-	-	1/10	330	330	330	-	-	
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	1000 Hours	-	-	-	-	-	-	-	31350	-	-	
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	2000 Hours	-	-	-	-	1450	31350	31350	-	-	-	
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	4000 Hours	-	-	-	31350	-	-	-	-	-	-	
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	-	-	-	330	1/10	330	330	-	-	-	
Test Group C - Package Assembly Integrity Tests																		
WBS	C1	AEC-Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1000	-	-	-	3900	1000	3900	3900	-	1000	1000
WBP	C2	ML-STDB83 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1000	-	-	-	3900	1000	3900	3900	-	1000	1000

QBS: Qual By Similarity, also known as Generic Data

Qual Device INA199A1QDCKRQ1 is qualified at MSL1 260C

Qual Device INA199A2QDCKRQ1 is qualified at MSL1 260C

Qual Device INA199A3QDCKRQ1 is qualified at MSL1 260C

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C

Grade 1 (or Q): -40C to +125C

Grade 2 (or T): -40C to +105C

Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2411-032

In performing change qualifications, Texas Instruments follows integrated circuit industry standards in performing defect mechanism analysis and failure mechanism-based accelerated environmental testing to ensure wafer fab process, assembly process and product quality and reliability. As encouraged by these standards, TI uses both product-specific and generic (family) data in qualifying its changes. For devices to be categorized as a 'product qualification family' for generic data purposes, they must share similar product, wafer fab process and assembly process elements. The applicability of generic data (also known at TI as Qualification by Similarity (QBS)) is determined by the Reliability Engineering function following these industry standards. Generic data is shown in the qualification report in columns titled "QBS Process" (for wafer fab process), "QBS Package" (for assembly process) and "QBS Product" (for product family).

ZVEI ID: SEM-DE-03 SEM-DE-02 SEM-DE-01 SEM-PW-09 SEM-PW-02 SEM-PW-13 SEM-PW-03 SEM-PA-18 SEM-PA-08 SEM-PA-05 SEM-PA-11 SEM-PA-07 SEM-PA-19 SEM-TF-01

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

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